

## Description

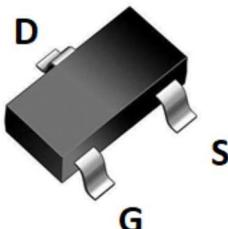
### PECJ N-channel Enhancement Mode Power MOSFET

#### Features

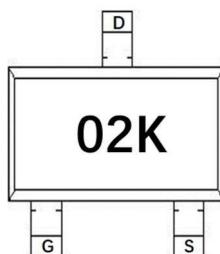
- 20V, 0.75A
- $R_{DS(ON)} < 380\text{m}\Omega$  @  $V_{GS} = 4.5\text{V}$
- $R_{DS(ON)} < 450\text{m}\Omega$  @  $V_{GS} = 2.5\text{V}$
- Advanced Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead free product is acquired
- ESD Protected: 2KV

#### Application

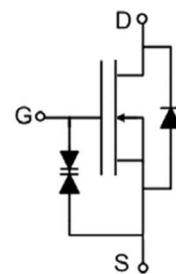
- Load Switch
- PWM Application
- Power management



SOT-23 top view



Marking and pin Assignment



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
02K	PECJ2002KT2	TAPING	SOT-23	-	-	-

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
$V_{DSS}$	Drain-Source Voltage		20	V
$V_{GSS}$	Gate-Source Voltage		$\pm 10$	V
$I_D$	Continuous Drain Current	$T_A = 25^\circ\text{C}$	0.75	A
		$T_A = 100^\circ\text{C}$	0.5	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>		3	A
$P_D$	Power Dissipation	$T_A = 25^\circ\text{C}$	0.35	W
$R_{\theta JA}$	Thermal Resistance, Junction to Case		417	$^\circ\text{C}/\text{W}$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$

# PECJ2002KT2

## Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise specified)

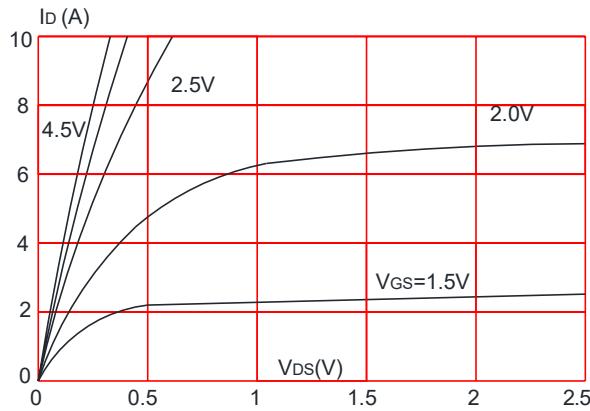
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$	20	-	-	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$ , $V_{GS}=0\text{V}$ ,	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 10\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.3	0.65	1	V
$R_{DS(\text{on})}$ note2	Static Drain-Source on-Resistance	$V_{GS}=4.5\text{V}$ , $I_D=0.5\text{A}$	-	250	380	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=0.3\text{A}$	-	350	450	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=10\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	79	-	pF
$C_{oss}$	Output Capacitance		-	13	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	9	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=10\text{V}$ , $I_D=0.3\text{A}$ , $V_{GS}=4.5\text{V}$	-	5	-	nC
$Q_{gs}$	Gate-Source Charge		-	0.8	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1.2	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10\text{V}$ , $I_D=0.5\text{A}$ , $R_{\text{GEN}}=3\Omega$ , $V_{GS}=4.5\text{V}$	-	6.7	-	ns
$t_r$	Turn-on Rise Time		-	4.8	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	17.3	-	ns
$t_f$	Turn-off Fall Time		-	7.4	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_s$	Maximum Continuous Drain to Source Diode Forward Current		-	-	0.75	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	3	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$ , $I_s=0.75\text{A}$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

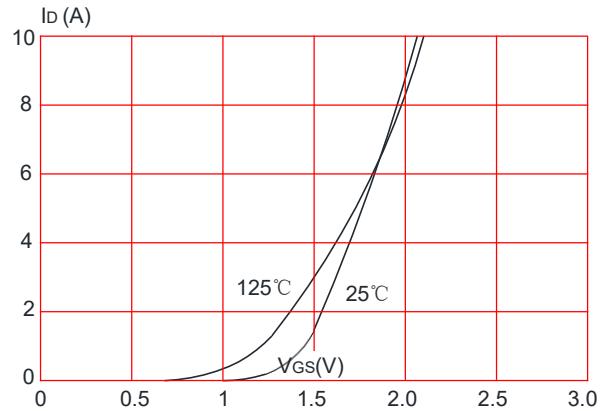
2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$ , Duty Cycle $\leq 0.5\%$

## Typical Performance Characteristics

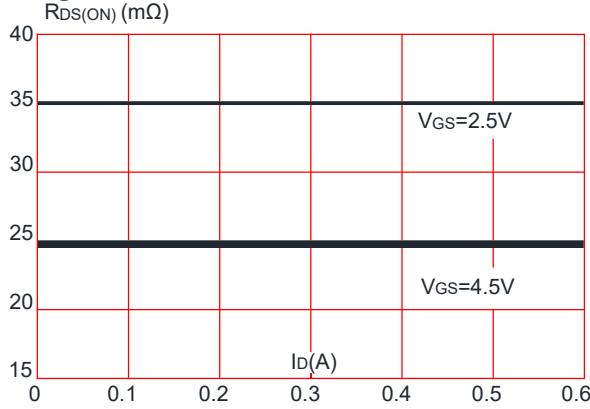
**Figure 1:** Output Characteristics



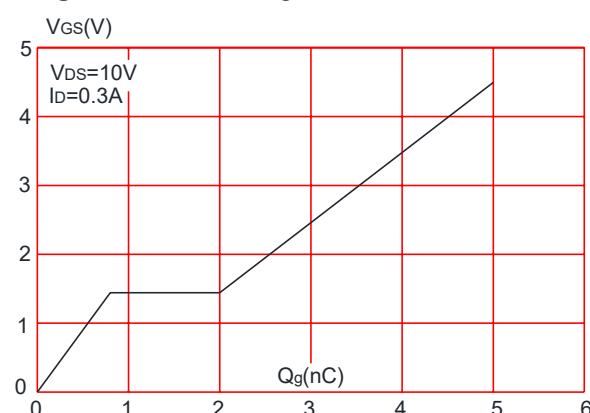
**Figure 2:** Typical Transfer Characteristics



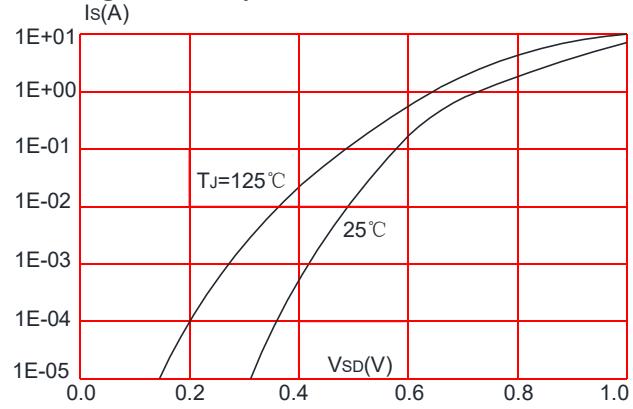
**Figure 3:** On-resistance vs. Drain Current



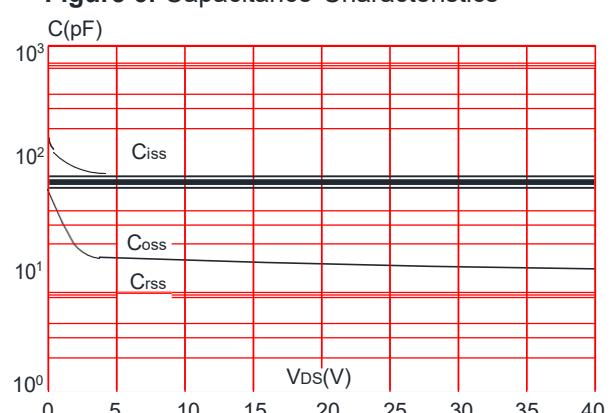
**Figure 5:** Gate Charge Characteristics



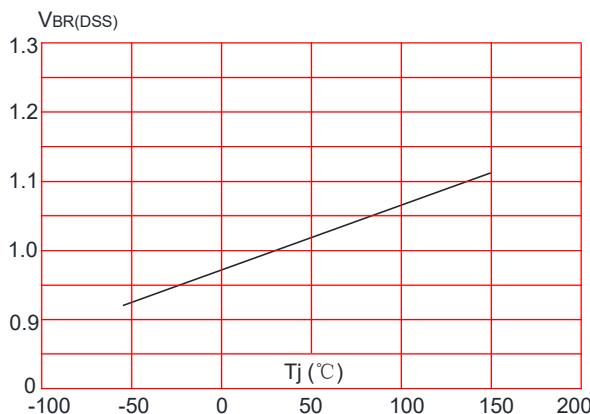
**Figure 4:** Body Diode Characteristics



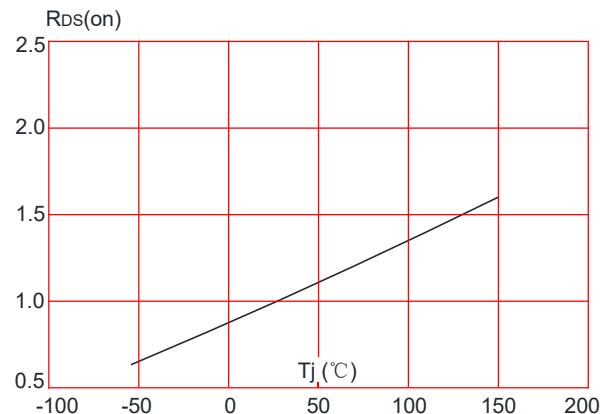
**Figure 6:** Capacitance Characteristics



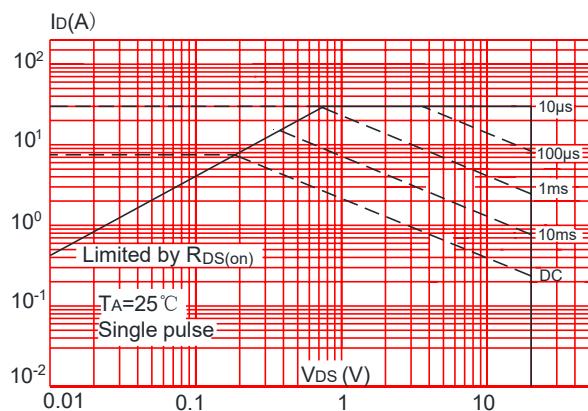
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



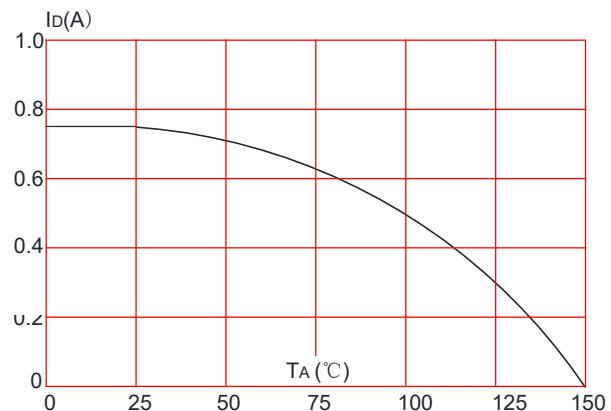
**Figure 8:** Normalized on Resistance vs. Junction Temperature



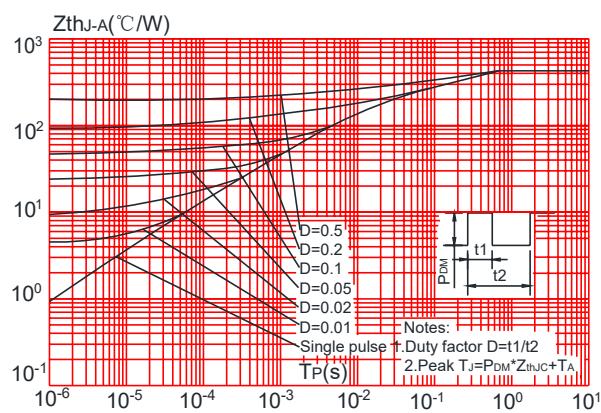
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



## Test Circuit

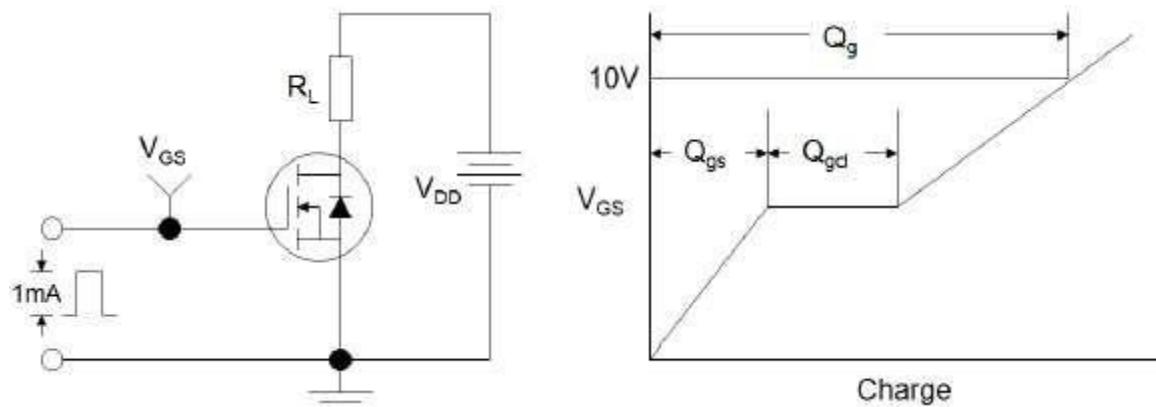


Figure 1: Gate Charge Test Circuit & Waveform

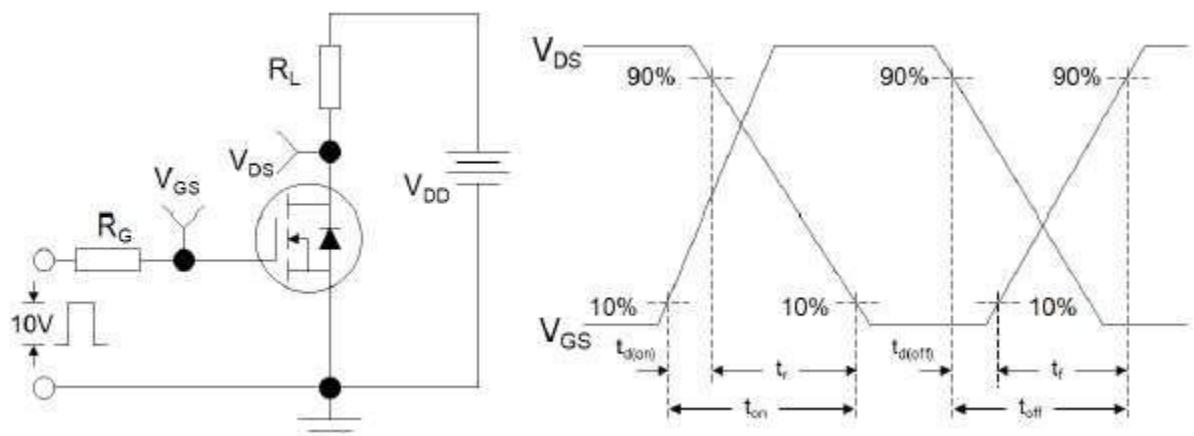


Figure 2: Resistive Switching Test Circuit & Waveforms

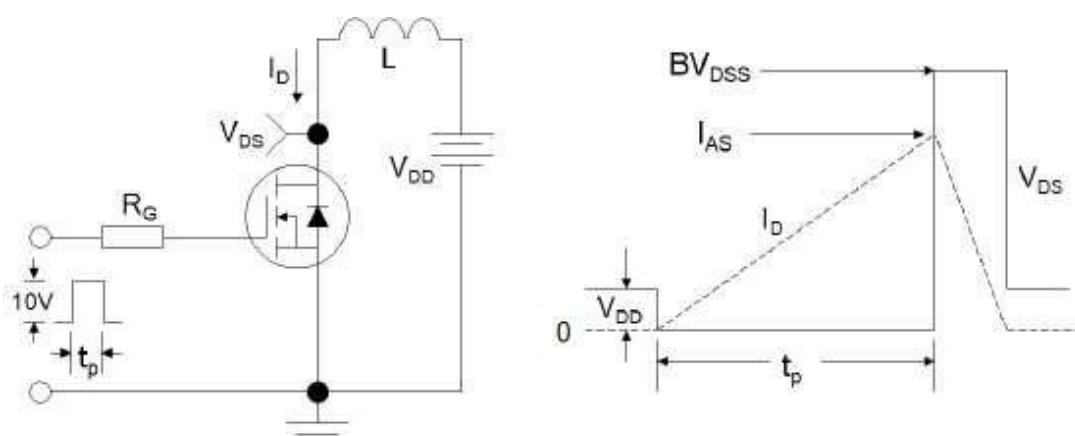
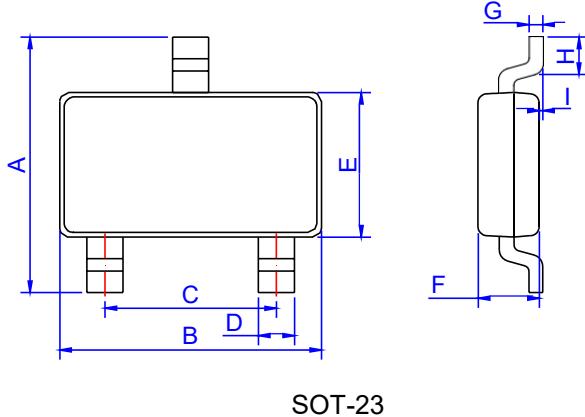


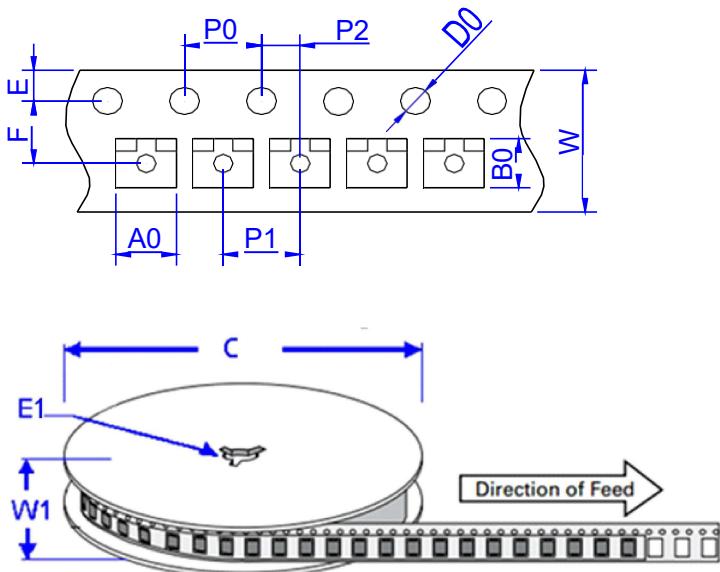
Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

## Package Mechanical Data-SOT-23



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

## Package Information-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	$3.15 \pm 0.3$	$0.124 \pm 0.012$
B0	$2.77 \pm 0.3$	$0.109 \pm 0.012$
C	178	7.0
D0	$1.50 \pm 0.1$	$0.059 \pm 0.004$
E	$1.75 \pm 0.2$	$0.069 \pm 0.008$
E1	$13.3 \pm 0.3$	$0.524 \pm 0.012$
F	$3.5 \pm 0.2$	$0.138 \pm 0.008$
P0	$4.00 \pm 0.2$	$0.157 \pm 0.008$
P1	$4.00 \pm 0.2$	$0.157 \pm 0.008$
P2	$2.00 \pm 0.2$	$0.079 \pm 0.008$
W	$8.00 \pm 0.2$	$0.315 \pm 0.008$
W1	$11.5 \pm 1.0$	$0.453 \pm 0.039$